



DMP2160U

P-CHANNEL ENHANCEMENT MODE MOSFET

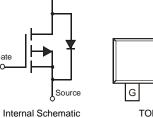
Features

- Low On-Resistance
 - $80 \text{ m}\Omega @ V_{GS} = -4.5 \text{V}$
 - $100 \text{ m}\Omega @ V_{GS} = -2.5 \text{V}$ •
 - 140 m Ω @ V_{GS} = -1.8V •
- Very Low Gate Threshold Voltage $V_{GS(th)} \le 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q 101 Standards for High Reliability

Mechanical Data

- Case: SOT-23 •
- Case Material: Molded Plastic, "Green" Molding Compound. -UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

TOP VIEW



TOP VIEW

D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteris	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	-20	V	
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 3)	$T_{A} = 25^{\circ}C$ $T_{A} = 70^{\circ}C$	ID	-3.2 -2.5	А
Pulsed Drain Current		I _{DM}	-13	А

SOT-23

Drain

Gate

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 3)	PD	1.4	W
Thermal Resistance, Junction to Ambient	$R_{ ext{ heta}JA}$	90	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on 1in² FR-4 PCB with 2 oz. Copper. t ≤ 10 sec.

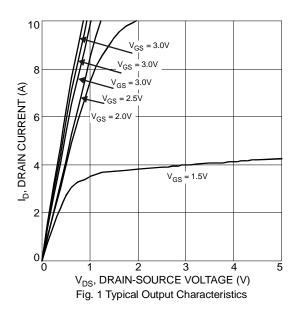


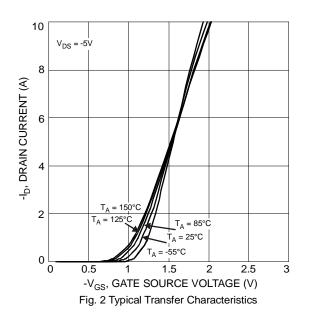
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Turn	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)	Symbol	IVIIN	Тур	wax	Unit	Test Condition
Drain-Source Breakdown Voltage		-20	i	i	V	
	BV _{DSS}		—			$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$	I _{DSS}			-1.0	μΑ	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		—	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
	-000		_	±800		$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)		i	i	i	i	i
Gate Threshold Voltage	V _{GS(th)}	-0.4	-0.6	-0.9	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			60	80		$V_{GS} = -4.5V, I_D = -1.5A$
Static Drain-Source On-Resistance	R _{DS (ON)}		73	100	mΩ	$V_{GS} = -2.5V, I_D = -1.2A$
			92	140		V _{GS} = -1.8V, I _D = -1.2A
Forward Transconductance	g fs	_	7	_	S	V _{DS} = -10V, I _D = -1.5A
Diode Forward Voltage (Note 4)	V _{SD}	_	_	-1.0	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 5)			_			
Input Capacitance	Ciss	_	627		pF	
Output Capacitance	Coss	_	64		pF	−V _{DS} = -10V, V _{GS} = 0V −f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	53		pF	
Gate Resistance	R _G	_	44.9		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$
Total Gate Charge	Qg	_	6.5	_	nC	
Gate-Source Charge	Q _{gs}	_	0.9		nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -3A
Gate-Drain Charge	Q _{qd}	_	1.5		nC	
Turn-On Delay Time	t _{D(on)}		12.5		ns	
Turn-On Rise Time	tr		10.3		ns	V _{DS} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{D(off)}		46.5		ns	$R_L = 10\Omega, R_G = 1.0\Omega, I_D = -1A$
Turn-Off Fall Time	t _f		22.2		ns	7

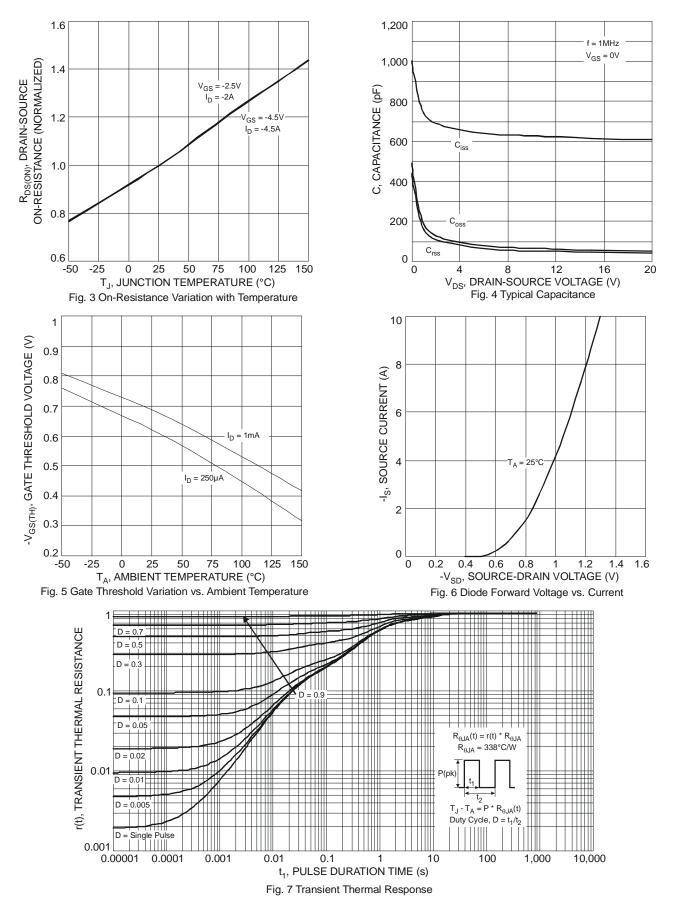
 Notes:
 4. Short duration pulse test used to minimize self-heating effect.

 5. Guaranteed by design. Not subject to product testing.









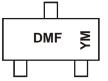


Ordering Information (Note 6)

Part Number	Case	Packaging
DMP2160U-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

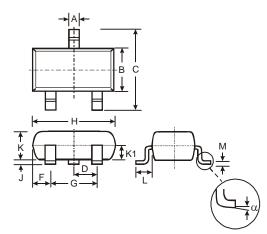


DMF = Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

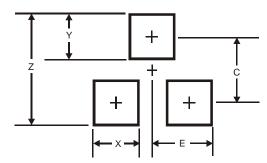
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Ма	y Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
в	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
κ	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
Μ	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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